



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

Device	BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
N-Channel	20V	35mΩ @ V _{GS} = 4.5V	4.6A
N-Charmer	200	43mΩ @ V _{GS} = 2.5V	4.2A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

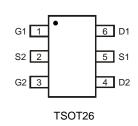
Applications

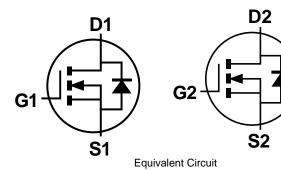
- Backlighting
- DC-DC Converters
- Power Management Functions

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.013 grams (Approximate)







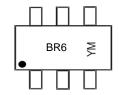
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2053UVT-7	TSOT26	3000 / Tape & Reel
DMN2053UVT-13	TSOT26	10,000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



BR6= Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: F = 2018) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year		2018		2019	2020		2021	2022		2023	2024		2025
Code)	F		G	Н		I	J		K	L		М
Mont	h	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code)	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Q1 Value	Unit		
Drain-Source Voltage	V _{DSS}	20	V		
Gate-Source Voltage	V _{GSS}	±12	V		
Continuous Drain Current (Note 6) V _{GS} = 4.5V Steady State		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	4.6 3.7	А
Maximum Continuous Body Diode Forward Current (Note 6	I _S	1.4	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	22	Α		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	173	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.1	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	108	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	37	C/VV
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

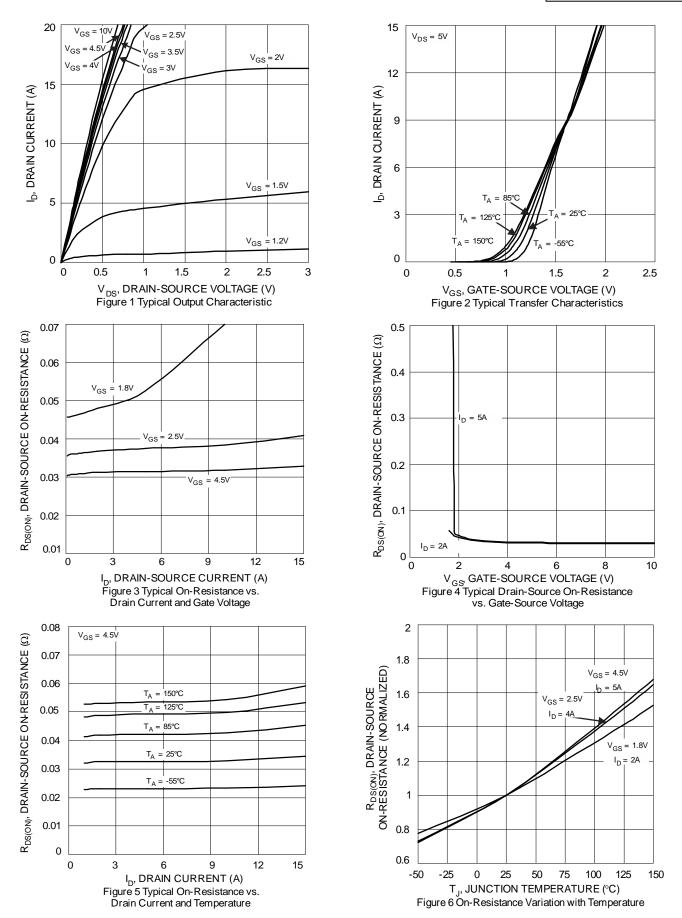
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_		1.0	μΑ	V _{DS} = 20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.4		1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
			_	35		$V_{GS} = 4.5V, I_D = 5.0A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_		43	mΩ	$V_{GS} = 2.5V, I_D = 4.0A$	
				56		$V_{GS} = 1.8V, I_D = 2.0A$	
Diode Forward Voltage	V_{SD}	1	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)					_		
Input Capacitance	C _{iss}	-	369	_		1/ 401/1/ 01/	
Output Capacitance	Coss	-	54	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	l	32	_		1 – 1.0101112	
Gate Resistance	R_g	l	4.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	l	3.6	_			
Gate-Source Charge	Q_{gs}		0.4	_	nC	$V_{GS} = 4.5V$, $V_{DS} = 10V$, $I_{D} = 6A$	
Gate-Drain Charge	Q_{gd}	_	1.0	_			
Turn-On Delay Time	t _{D(ON)}	_	2.6	_			
Turn-On Rise Time	t _R	_	3.0	_		$V_{DS} = 10V, V_{GS} = 5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	12.5	_	ns	$R_G = 6\Omega$, $I_D = 6A$	
Turn-Off Fall Time	t _F	_	3.6	_			
Reverse Recovery Time	t _{RR}	_	6.0	_	ns	1 4 4 4:/44 4000///-	
Reverse Recovery Charge	Q _{RR}	_	0.9	_	nC	I _F = 1A, di/dt = 100A/μs	

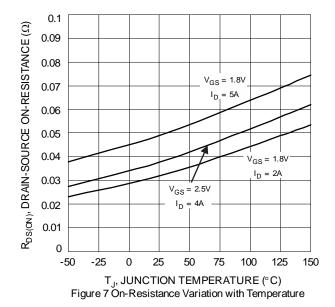
Notes:

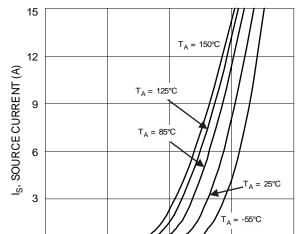
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.









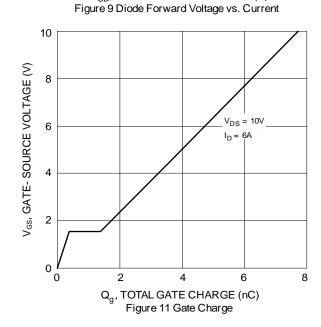


0.6

V_{SD}, SOURCE-DRAIN VOLTAGE (V)

0.9

1.2



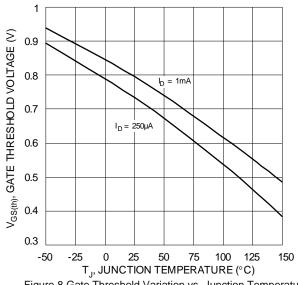
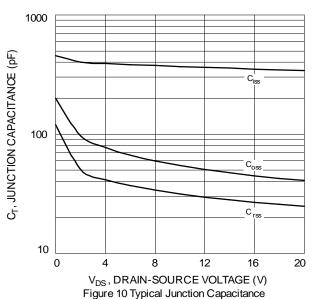


Figure 8 Gate Threshold Variation vs. Junction Temperature



100 R_{DS(on)} P_W = 100µs P_W = 100µs P_W = 100µs P_W = 100ms P_W

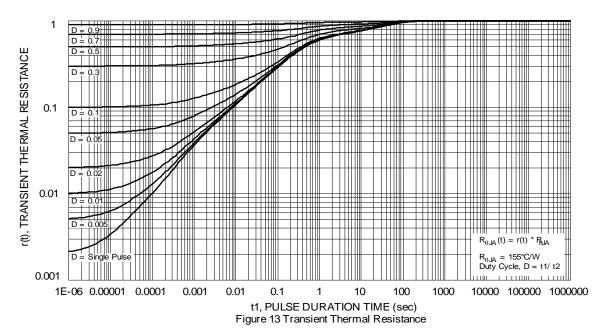
Figure 12 SOA, Safe Operation Area

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0 |

0.3



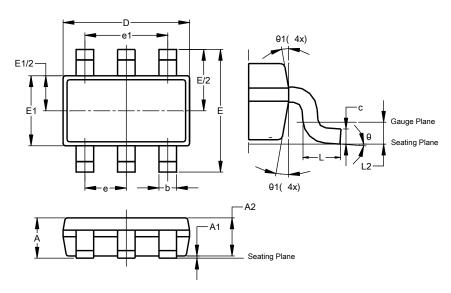




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

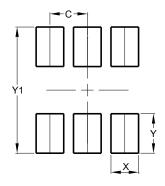


TSOT26							
Dim	Min	Max	Тур				
Α	_	1.00	_				
A1	0.010	0.100	_				
A2	0.840	0.900	_				
D	2.800	3.000	2.900				
Е	2	2.800 BS	С				
E1	1.500	1.700	1.600				
b	0.300	0.450	_				
С	0.120	0.120 0.200 —					
е	0.950 BSC						
e1	1	.900 BS	С				
L	0.30	0.30 0.50 —					
L2	0	.250 BS	С				
θ	0°	8°	4°				
θ1	4°	12°	_				
Δ	II Dimen	sions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Υ	1.000
Y1	3.199



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